

Applicant: Kazuhide Kumakura et al.

Confirmation No.: 6664

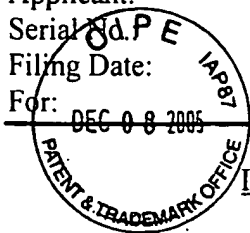
Serial: 10/532,782

Att'y Docket No.: 14321.71

Filing Date: April 25, 2005

Art Unit: 2812

For: SUBSTRATE FOR NITRIDE SEMICONDUCTOR GROWTH

INFORMATION DISCLOSURE CITATIONS MADE BY APPLICANTU.S. Patent Documents

Examiner Initial*	Document Number	Issue Date	Name
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Foreign Patent Documents

Examiner Initial*	Document Number	Publication Date	Country or Patent Office	Translation
EDJ 1	02-141495	05/30/1990	Japan	No
EDJ 2	11-060395	03/02/1999	Japan	No
EDJ 3	11-340147	12/10/1999	Japan	No
EDJ 4	WO 02/12598 A1	02/14/2002	PCT	N/A

Other Documents

(including author, title, pertinent pages, etc.)

Examiner
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EDJ 5	Hyun-Jeong Kim et al., <i>Effects of Reactive Ion Beam Treatment of a Sapphire Surface to Optimize the Deposition of GaN Films</i> , Journal of Applied Physics, Vol. 87, No. 11, June 1, 2000, pp. 7940-7945.
EDJ 6	Cyril Pernot et al., <i>Low-Intensity Ultraviolet Photodetectors Based on AlGaIn</i> , Japanese Journal Applied Physics, Vol. 38, 1999, pp. L487-L489.
EDJ 7	H. Amano et al., <i>Metalorganic Vapor Phase Epitaxial Growth of a High Quality GaN Film Using an AlN Buffer Layer</i> , Applied Physics Letters, Vol. 48, No. 5, February 3, 1986, pp. 353-355.
EDJ 8	Shuji Nakamura, <i>GaN Growth Using GaN Buffer Layer</i> , Japanese Journal of Applied Physics, Vol. 30, No. 10A, October 1991, pp. L1705-L1707.

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12/2/05

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Form PTO-1449

Sheet 2 of 2

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References Cited by Applicants

While the filing of Information Disclosure Statements is voluntary, the procedure is governed by the guidelines of Section 609 of the Manual of Patent Examining Procedure and 37 C.F.R. §§ 1.97 and 1.98. To be considered a proper Information Disclosure Statement, Form PTO-1449 shall be accompanied by a copy of each listed patent or publication or other item of information and a translation of the pertinent portions of foreign documents (if an existing translation is readily available to the applicant), an explanation of relevance of each reference not in the English language, and should be submitted in a timely manner as set out in MPEP Sec. 609.

Examiners will consider all citations submitted in conformance with 37 C.F.R. § 1.98 and MPEP Sec. 609 and place their initials adjacent the citations in the spaces provided on this form. Examiners will also initial citations not in conformance with the guidelines which may have been considered. A reference may be considered by the Examiner for any reason whether or not the citation is in full conformance with the guidelines. A line will be drawn through a citation if it is not in conformance with the guidelines AND has not been considered. A copy of the submitted form, as reviewed by the Examiner, will be returned to the applicant with the next communication. The original of the form will be entered into the application file.

Each citation initialed by the Examiner will be printed on the issued patent in the same manner as references cited by the Examiner on Form PTO-892.

The reference designations "A1," "A2," etc. (referring to Applicant's reference 1, Applicant's reference 2, etc.) will be used by the Examiner in the same manner as Examiner's reference designations "A," "B," "C," etc. on Office Action Form PTO-1142.

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